

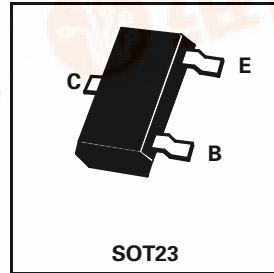
**SOT23 PNP SILICON PLANAR
MEDIUM POWER TRANSISTOR**

BCX17

ISSUE 4 – MARCH 2001

PARTMARKING DETAILS – BCX17 – T1
BCX17R – T4

COMPLIMENTARY TYPES - BCX19



ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Emitter Voltage	V_{CES}	-50	V
Collector-Emitter Voltage ($I_C = -10mA$)	V_{CEO}	-45	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-500	mA
Peak Collector Current	I_{CM}	-1000	mA
Peak Emitter Current	I_{EM}	-1000	mA
Base Current	I_B	-100	mA
Peak Base Current	I_{BM}	-200	mA
Power Dissipation at $T_{amb}=25^\circ C$	P_{tot}	330	mW
Operating and Storage Temperature Range	$T_j:T_{stg}$	-55 to +150	$^\circ C$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^\circ C$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Cut-Off Current	I_{CBO}			-100 -200	nA μA	$I_E = 0, V_{CB} = -20V$ $I_E = 0, V_{CB} = -20V, T_j = 150^\circ C$
Emitter-Base Cut-Off Current	I_{EBO}			-10	μA	$I_C = 0, V_{EB} = -1V$
Base-Emitter Voltage	V_{BE}			-1.2	V	$I_C = -500mA, V_{CE} = -1V^*$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			-620	mV	$I_C = -500mA, I_B = -50mA^*$
Static Forward Current Transfer Ratio	h_{FE}	100 70 40		600		$I_C = -100mA, V_{CE} = -1V$ $I_C = -300mA, V_{CE} = -1V^*$ $I_C = -500mA, V_{CE} = -1V^*$
Transition Frequency	f_T		100		MHz	$I_C = -10mA, V_{CE} = -5V$ $f = 35MHz$
Output Capacitance	C_{obo}		8.0		pF	$V_{CB} = -10V, f = 1MHz$

*Measured under pulsed conditions.
Spice parameter data is available upon request for this device